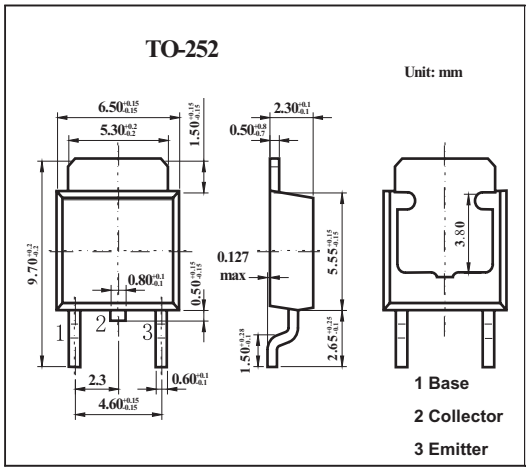
TY Semicondutor®

Product specification

2SC3632-Z



■ Features

- High voltage V_{CEO}=600V

  High speed tf＜0.5μs

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	600	V
Collector to emitter voltage	V_{CES}	600	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current *1	I_{CP}	2	A
Collector current	I_C	1	A
Total power dissipation Ta= 25℃*2	P_T	2	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

*1 pw≤10ms,Duty cycle≤50%

*2 when mounted on ceramic substrate of 7.5cm^{2}X0.7mm

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
collecotr cutoff current	I_{CBO}	V_{CB}=600V,IE=0			10	μA
Emitter cutoff current	I_{EBO}	V_{EB}=7V,IC=0			10	μA
DC Current Gain	h_{FE}	V_{CE}=5V,I_C=100mA	30	55	120	
		V_{CE}=5V,I_C=100mA	5	7		
Collector saturation voltage	$V_{CE(sat)}$	I_C=400mA,I_B=80mA		0.35	1.0	V
Base to saturation voltage	$V_{BE(sat)}$	IC=400mA,I_B=80mA		0.9	1.2	V
Gain Bandwidth Product	fT	V_{CE}=5V,I_E=-50mA		30		MHz
Output capacitance	cob	V_{CB}=10V,I_E=0A,f=1MHz		14		pF
Turn-on time	t_{on}	I_C=0.5A,R_L=500Ω		0.1	0.5	μs
Storage time	t_{stg}	I_{B1}=-I_{B2}=0.1A		4.0	5.0	μs
Fall time	t_f	V_{CC}=250V		0.2	0.5	μs

■ h_{FE} Classification

Marking	M	L	K
hFE	30 to 60	40 to 80	60 to 120